

DATA SHEET

BLF544B

UHF push-pull power MOS
transistor

Product specification

October 1992

UHF push-pull power MOS transistor

BLF544B

FEATURES

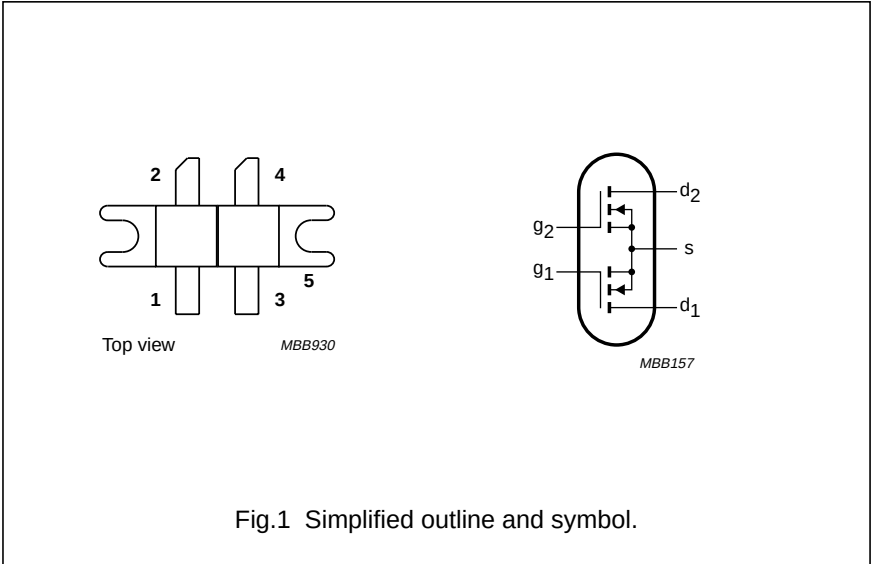
- High power gain
- Easy power control
- Good thermal stability
- Gold metallization ensures excellent reliability
- Designed for broadband operation.

DESCRIPTION

Silicon N-channel enhancement mode vertical D-MOS push-pull transistor designed for communications transmitter applications in the UHF frequency range.

The transistor is encapsulated in a 4-lead, SOT268 balanced flange envelope, with two ceramic caps. The mounting flange provides the common source connection for the transistors.

PIN CONFIGURATION



CAUTION

The device is supplied in an antistatic package. The gate-source input must be protected against static charge during transport and handling.

PINNING - SOT268

PIN	DESCRIPTION
1	gate 1
2	drain 1
3	gate 2
4	drain 2
5	source

WARNING

Product and environmental safety - toxic materials
This product contains beryllium oxide. The product is entirely safe provided that the BeO discs are not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

QUICK REFERENCE DATA

RF performance at $T_h = 25\text{ }^{\circ}\text{C}$ in a push-pull common source test circuit.

MODE OF OPERATION	f (MHz)	V _{DS} (V)	P _L (W)	G _p (dB)	η _D (%)
CW, class-B	500	28	20	> 12	> 50

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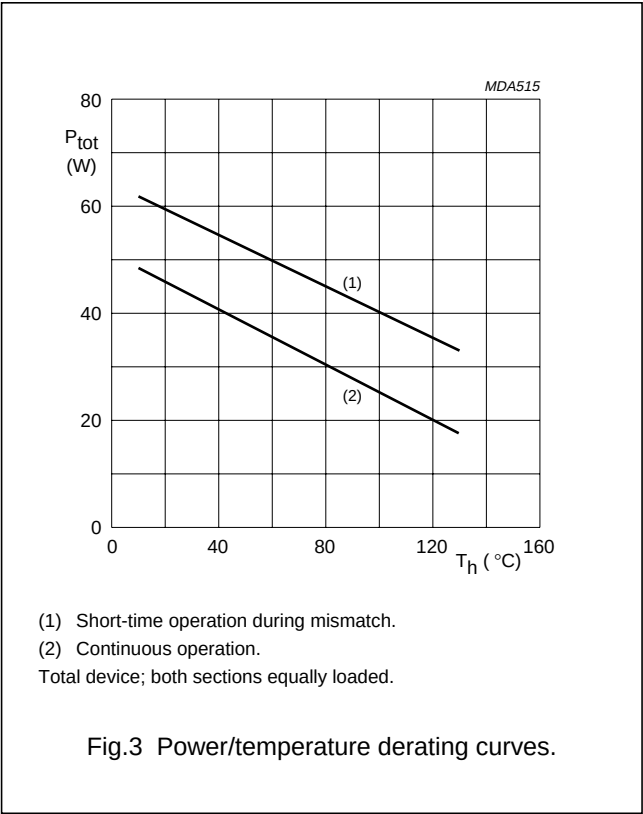
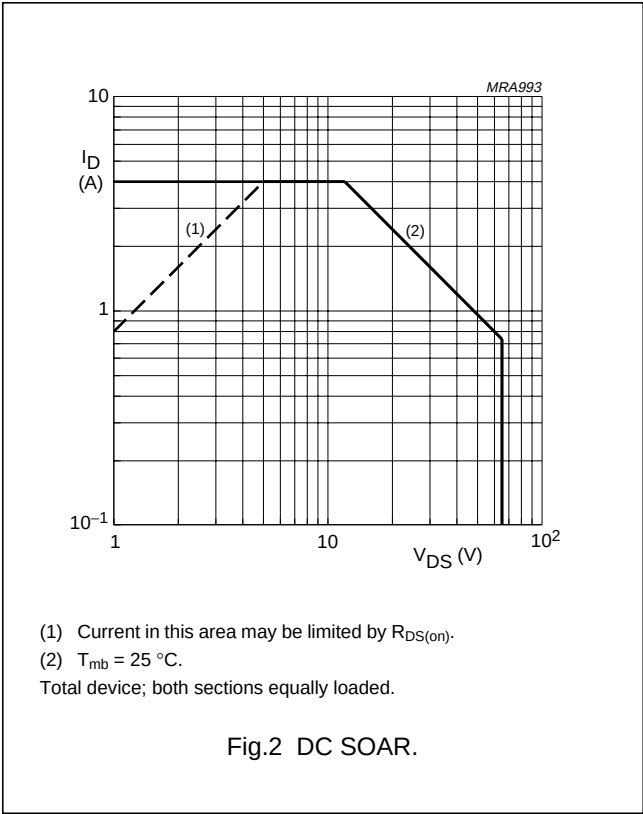
LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).
Per transistor section unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	drain-source voltage		–	65	V
$\pm V_{GS}$	gate-source voltage		–	20	V
I_D	DC drain current		–	2	A
P_{tot}	total power dissipation	up to $T_{mb} = 25\text{ }^{\circ}\text{C}$; total device; both sections equally loaded	–	48	W
T_{stg}	storage temperature		–65	150	$^{\circ}\text{C}$
T_j	junction temperature		–	200	$^{\circ}\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	THERMAL RESISTANCE
$R_{th\ j-mb}$	thermal resistance from junction to mounting base	total device; both sections equally loaded	3.7 K/W
$R_{th\ mb-h}$	thermal resistance from mounting base to heatsink	total device; both sections equally loaded	0.25 K/W



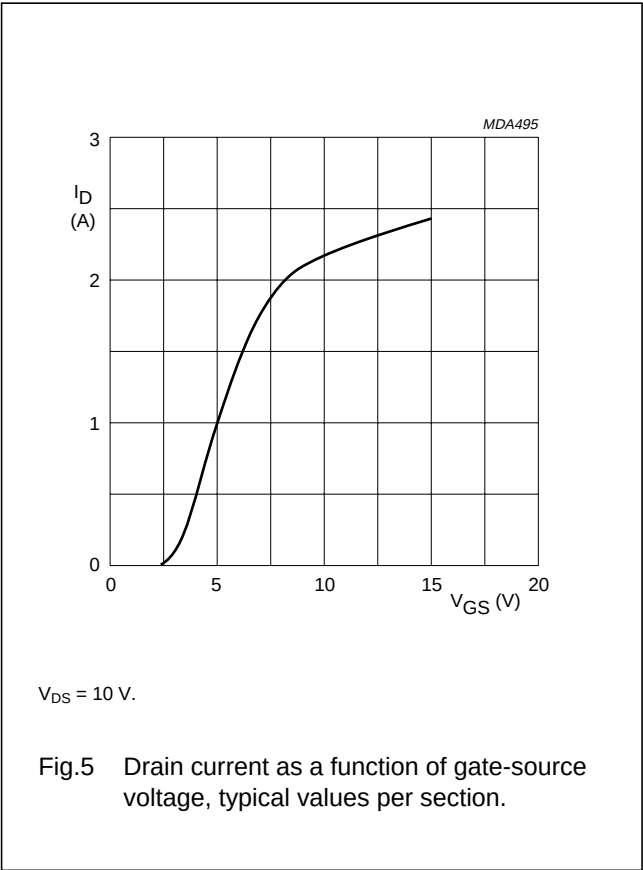
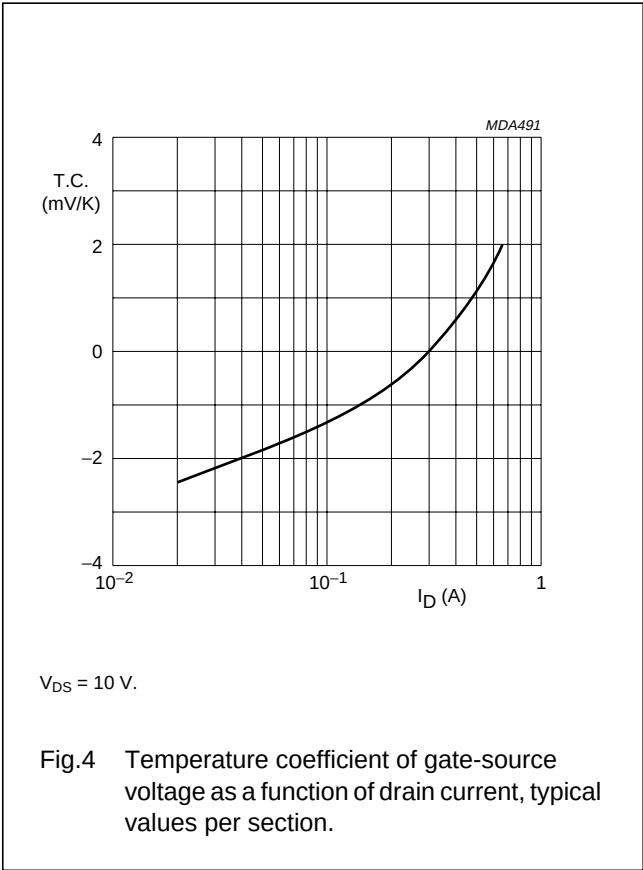
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CHARACTERISTICS (per section)

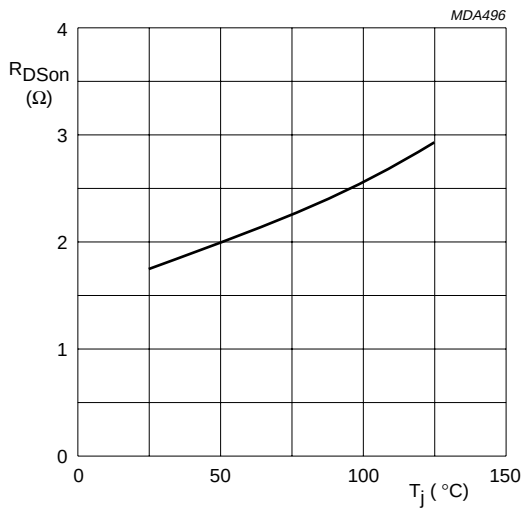
T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 5 mA; V _{GS} = 0	65	–	–	V
I _{DSS}	drain-source leakage current	V _{GS} = 0; V _{DS} = 28 V	–	–	0.5	mA
I _{GSS}	gate-source leakage current	±V _{GS} = 20 V; V _{DS} = 0	–	–	1	µA
V _{GS(th)}	gate-source threshold voltage	I _D = 20 mA; V _{DS} = 10 V	1	–	4	V
g _{fs}	forward transconductance	I _D = 0.6 A; V _{DS} = 10 V	300	450	–	mS
R _{DS(on)}	drain-source on-state resistance	I _D = 0.6 A; V _{GS} = 10 V	–	0.7	2.5	Ω
I _{DSX}	on-state drain current	V _{GS} = 15 V; V _{DS} = 10 V	–	2.4	–	A
C _{is}	input capacitance	V _{GS} = 0; V _{DS} = 28 V; f = 1 MHz	–	16	–	pF
C _{os}	output capacitance	V _{GS} = 0; V _{DS} = 28 V; f = 1 MHz	–	12	–	pF
C _{rs}	feedback capacitance	V _{GS} = 0; V _{DS} = 28 V; f = 1 MHz	–	3.2	–	pF



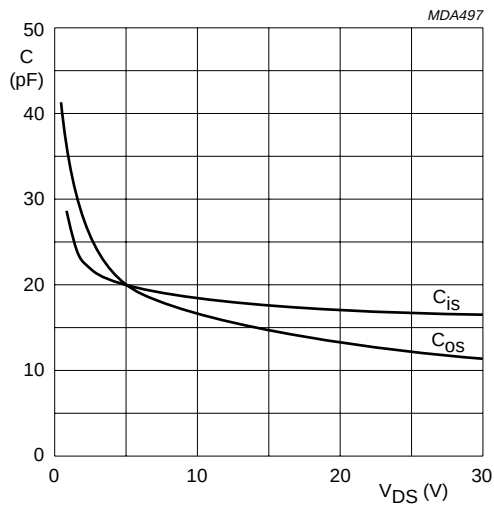
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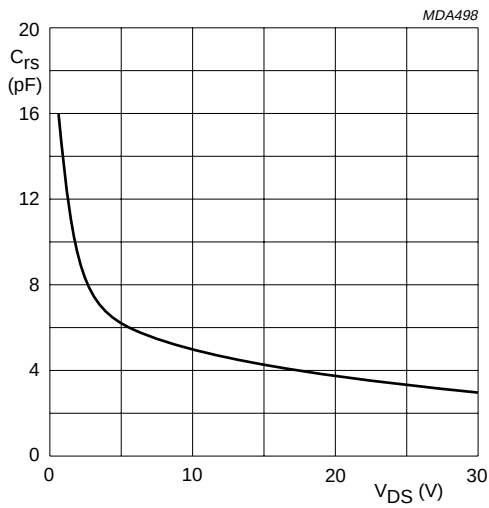
$I_D = 0.6\text{ A}$; $V_{GS} = 10\text{ V}$.

Fig.6 Drain-source on-state resistance as a function of junction temperature, typical values per section.



$V_{GS} = 0$; $f = 1\text{ MHz}$.

Fig.7 Input and output capacitance as functions of drain-source voltage, typical values per section.



$V_{GS} = 0$; $f = 1\text{ MHz}$.

Fig.8 Feedback capacitance as a function of drain-source voltage, typical values per section.

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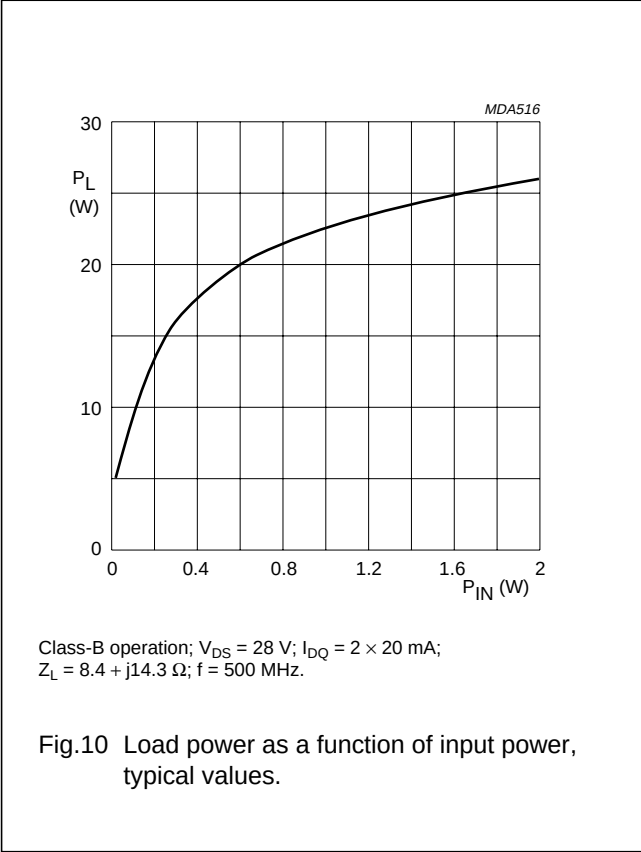
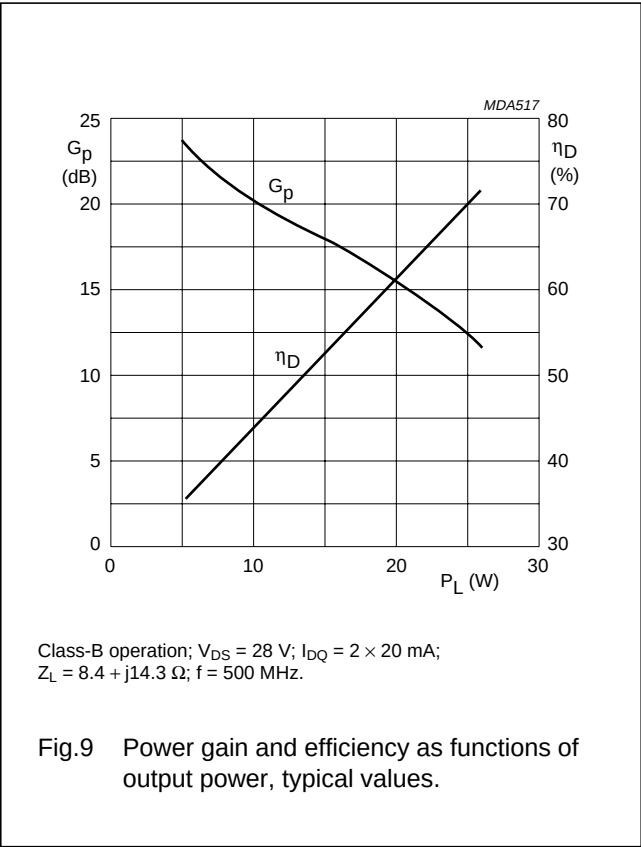
APPLICATION INFORMATION FOR CLASS-B OPERATION

$T_h = 25\text{ }^{\circ}\text{C}$; $R_{th\text{ mb-h}} = 0.4\text{ K/W}$; unless otherwise specified.
RF performance in a push-pull, common source, class-B test circuit.

MODE OF OPERATION	f (MHz)	V _{DS} (V)	I _{DQ} (mA)	P _L (W)	G _p (dB)	η _D (%)
CW, class-B	500	28	2 × 20	20	> 12 typ. 15	> 50 typ. 60

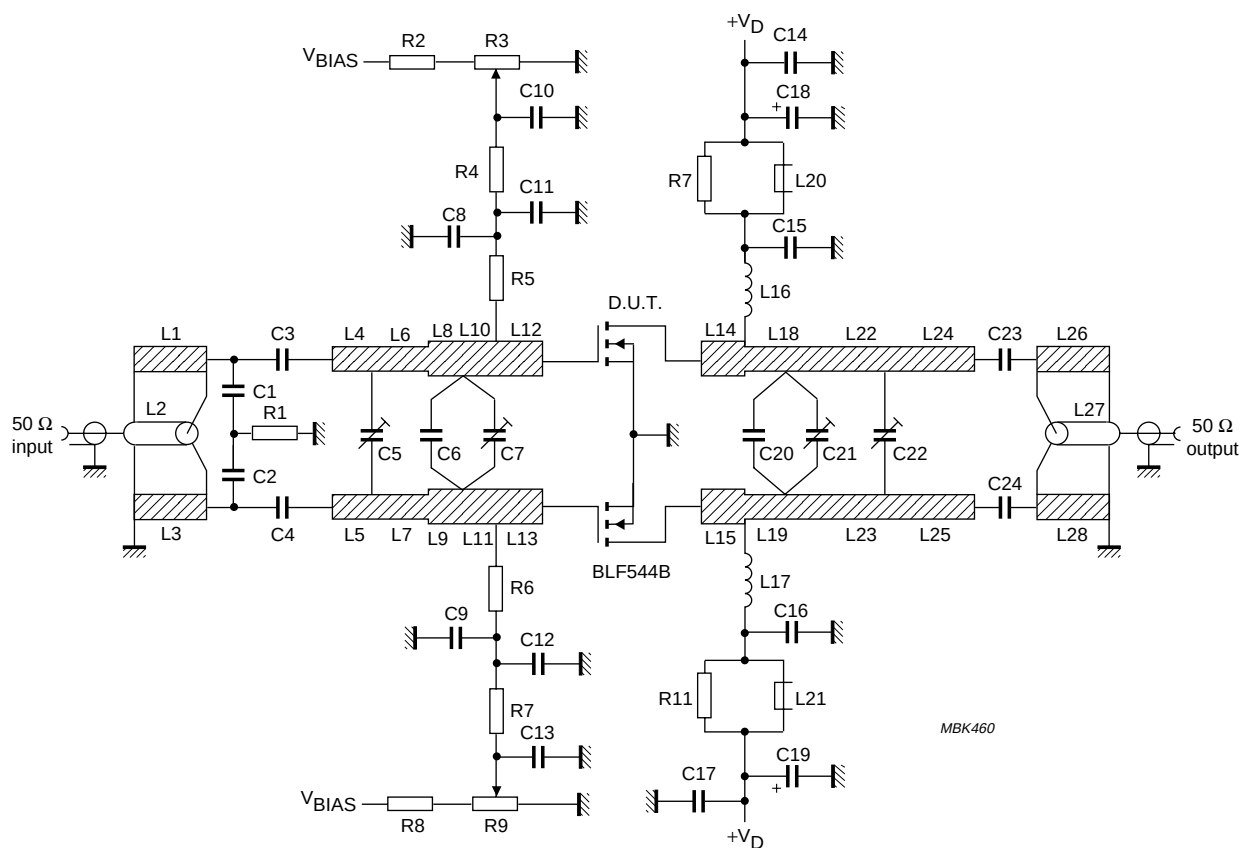
Ruggedness in class-B operation

The BLF544B is capable of withstanding a load mismatch corresponding to VSWR = 50 through all phases, under the following conditions:
 $V_{DS} = 28\text{ V}$, $f = 500\text{ MHz}$ at rated output power.



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f = 500 MHz.

Fig.11 Test circuit for class-B operation.

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List of components (class-B test circuit)

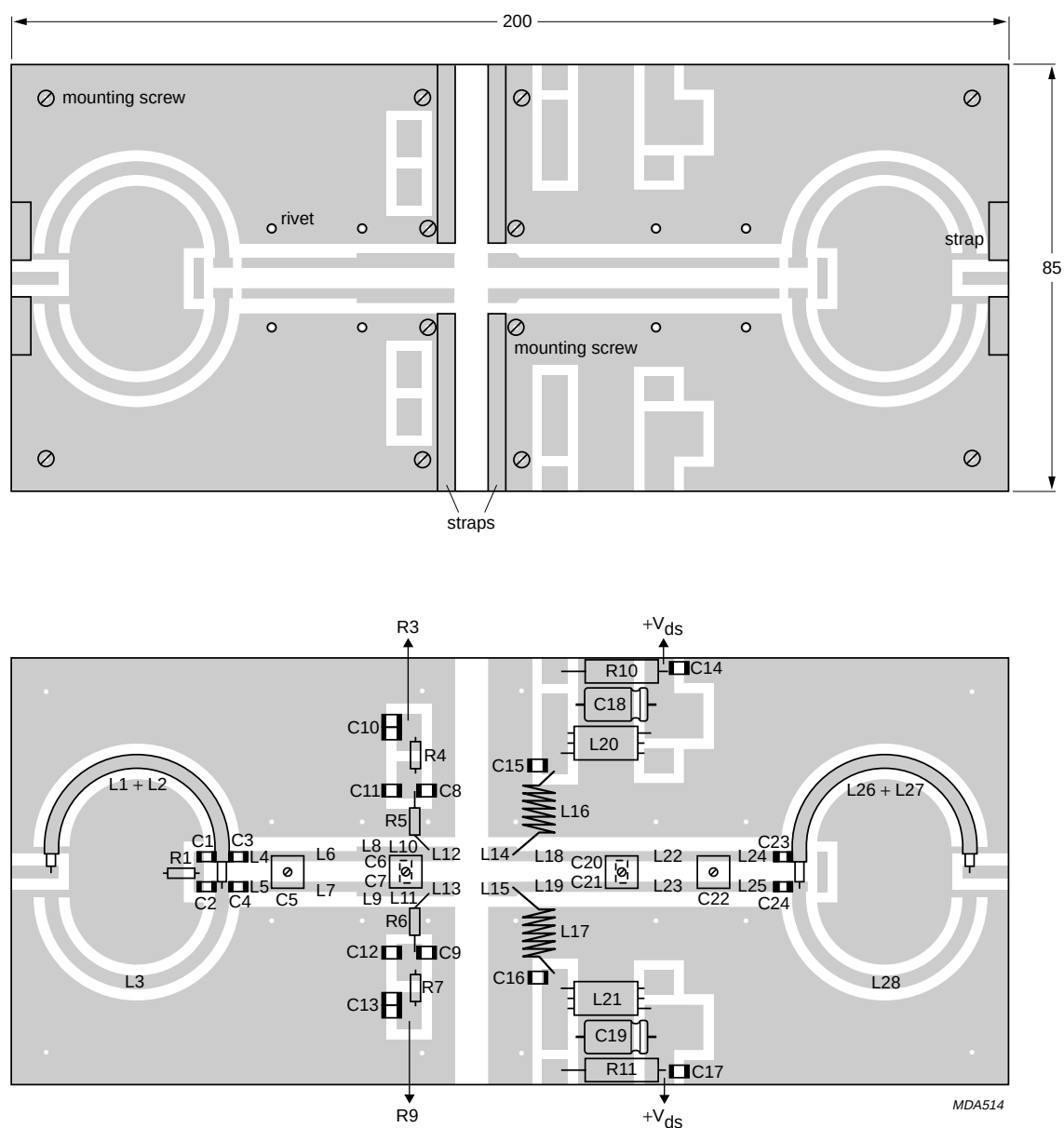
COMPONENT	DESCRIPTION	VALUE	DIMENSIONS	CATALOGUE NO.
C1, C2	multilayer ceramic chip capacitor (note 1)	9.1 pF, 500 V		
C3, C4, C6	multilayer ceramic chip capacitor (note 1)	18 pF, 500 V		
C5	film dielectric trimmer	2 to 9 pF		2222 809 09005
C7, C21, C22	film dielectric trimmer	2 to 18 pF		2222 809 09006
C8, C9, C15, C16	multilayer ceramic chip capacitor (note 1)	390 pF, 500 V		
C10, C13	multilayer ceramic chip capacitor	2 × 100 nF in parallel, 50 V		2222 852 47104
C11, C12, C14, C17	multilayer ceramic chip capacitor	100 nF, 50 V		2222 852 47104
C18, C19	electrolytic capacitor	10 µF, 63 V		2222 030 38109
C20	multilayer ceramic chip capacitor (note 1)	6.8 pF, 500 V		
C23, C24	multilayer ceramic chip capacitor (note 1)	16 pF, 500 V		
L1, L3, L26, L28	stripline (note 2)	50 Ω	56 × 2.4 mm	
L2	semi-rigid cable (note 3)	50 Ω	ext. dia. 2.2 mm ext. conductor length 56 mm	
L4, L5	stripline (note 2)	56 Ω	8 × 2 mm	
L6, L7	stripline (note 2)	56 Ω	15.5 × 2 mm	
L8, L9	stripline (note 2)	42 Ω	10 × 3 mm	
L10, L11	stripline (note 2)	42 Ω	5 × 3 mm	
L12, L13, L14, L15	stripline (note 2)	42 Ω	6 × 3 mm	
L16, L17	6 turns enamelled 1 mm copper wire	124 nH	length 8.5 mm int. dia. 5.4 mm leads 2 × 5 mm	
L18, L19	stripline (note 2)	56 Ω	22 × 2 mm	
L20, L21	grade 3B Ferroxcube RF choke			4312 020 36642
L22, L23	stripline (note 2)	56 Ω	18 × 2 mm	
L24, L25	stripline (note 2)	56 Ω	16 × 2 mm	
L27	semi-rigid cable (note 3)	50 Ω	ext. dia. 2.2 mm ext. conductor length 56 mm	
R1	0.4 W metal film resistor	5.62 Ω		2322 151 75628
R2, R8	0.4 W metal film resistor	11.5 kΩ		2322 151 71159
R3, R9	10 turns potentiometer	5 kΩ		
R4, R7	0.4 W metal film resistor	590 Ω		2322 151 75901
R5, R6	0.4 W metal film resistor	46.4 Ω		2322 151 74649
R10, R11	1 W metal film resistor	10 Ω		2322 153 51009

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Notes

1. American Technical Ceramics (ATC) capacitor, type 100B or other capacitor of the same quality.
2. The striplines are on a double copper-clad printed circuit board, with epoxy glass dielectric ($\epsilon_r = 2.2$), thickness $\frac{1}{32}$ inch.
3. Semi-rigid cables L2 and L27 are soldered on to striplines L1 and L26.



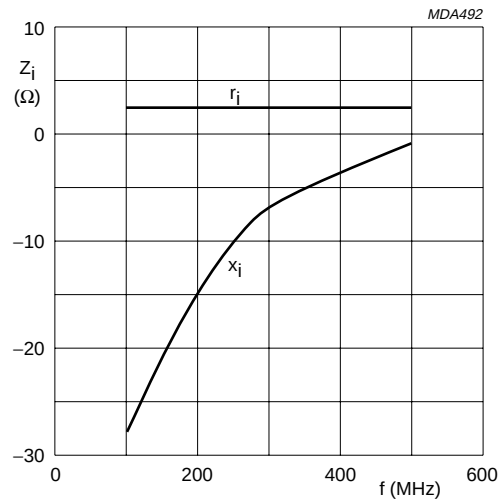
The circuit and components are situated on one side of the epoxy fibre-glass board, the other side being fully metallized to serve as a ground. Earth connections are made by means of copper straps and hollow rivets for a direct contact between the upper and lower sheets.

Dimensions in mm.

Fig.12 Component layout for 500 MHz test circuit.

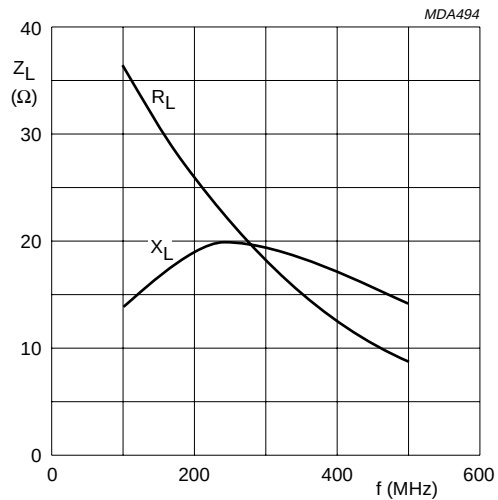
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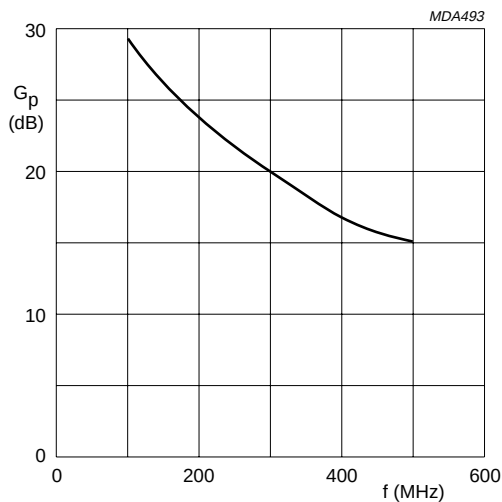
Class-B operation; $V_{DS} = 28\text{ V}$; $I_{DQ} = 2 \times 20\text{ mA}$; $P_L = 20\text{ W}$.

Fig.13 Input impedance as a function of frequency (series components), typical values per section.



Class-B operation; $V_{DS} = 28\text{ V}$; $I_{DQ} = 2 \times 20\text{ mA}$; $P_L = 20\text{ W}$.

Fig.14 Load impedance as a function of frequency (series components), typical values per section.



Class-B operation; $V_{DS} = 28\text{ V}$; $I_{DQ} = 2 \times 20\text{ mA}$; $P_L = 20\text{ W}$.

Fig.15 Power gain as a function of frequency, typical values per section.

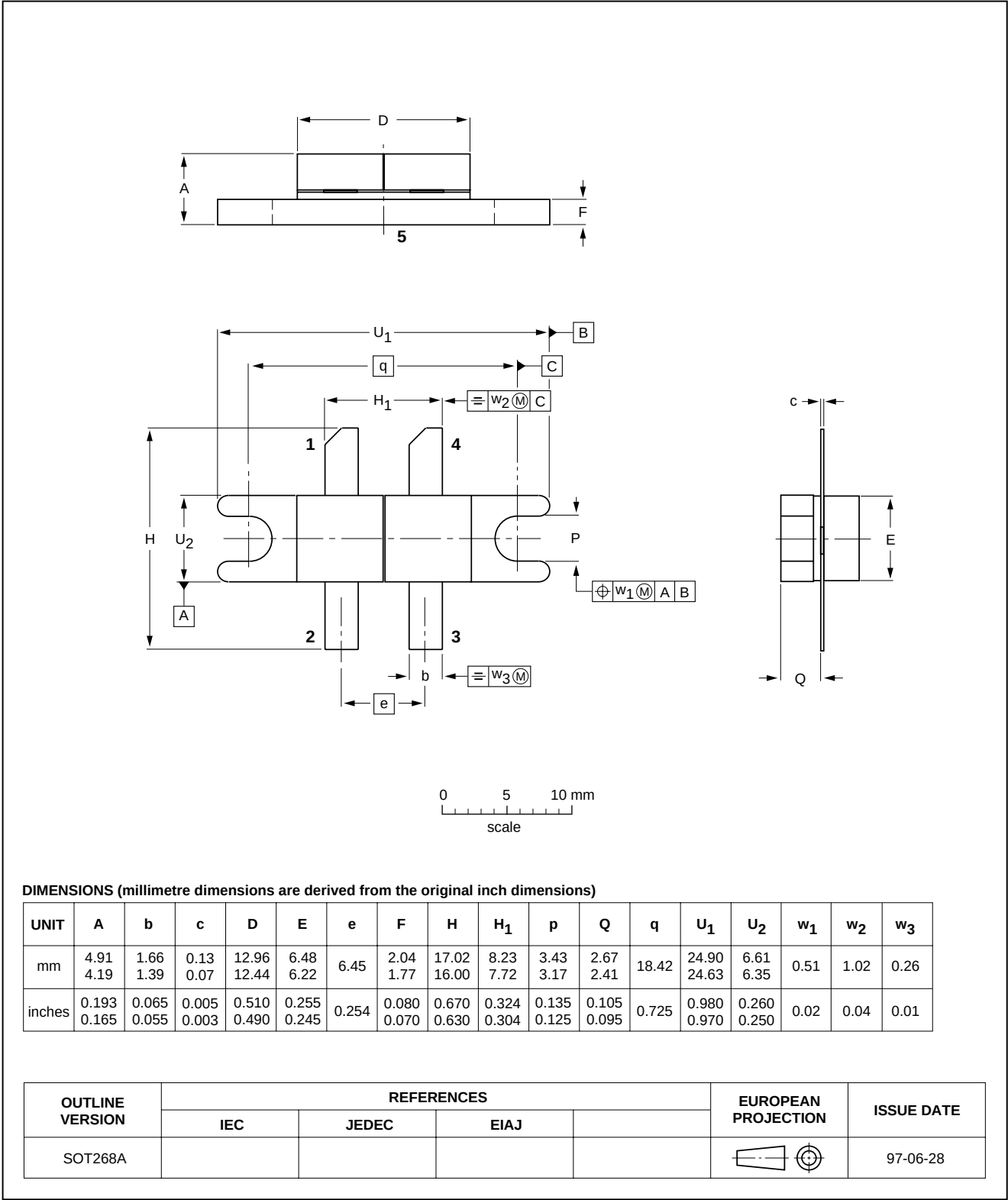
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PACKAGE OUTLINE

Flanged double-ended ceramic package; 2 mounting holes; 4 leads

SOT268A



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DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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